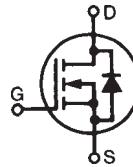


**Polar™ HiPerFET™
Power MOSFET**

IXFL100N50P

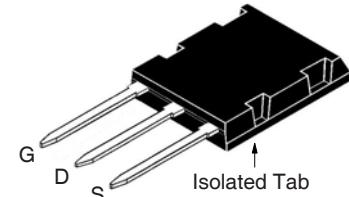
(Electrically Isolated Tab)

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



V_{DSS} = 500V
 I_{D25} = 68A
 $R_{DS(on)}$ ≤ 52mΩ
 t_{rr} ≤ 200ns

ISOPLUS264



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	500		V
V_{GSS}	Continuous	±30		V
V_{GSM}	Transient	±40		V
I_{D25}	$T_C = 25^\circ\text{C}$	68		A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	250		A
I_A	$T_C = 25^\circ\text{C}$	100		A
E_{AS}	$T_C = 25^\circ\text{C}$	5		J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	20		V/ns
P_D	$T_C = 25^\circ\text{C}$	625		W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	Maximum Lead Temperature for Soldering	300		°C
T_{SOLD}	Plastic Body for 10s	260		°C
F_c	Mounting Force	40..120 / 9..27		N/lb.
V_{ISOL}	50/60 Hz, RMS $t = 1\text{ min}$ $I_{ISOL} \leq 1\text{ mA}$ $t = 1\text{ s}$	2500 3000	V~ V~	
Weight		8		g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 3\text{mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{mA}$	3.0		V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$			$25\text{ }\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 50\text{A}$, Note 1			52 mΩ

Features

- Silicon Chip on Direct-Copper-Bond Substrate
 - High Power Dissipation
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

Applications

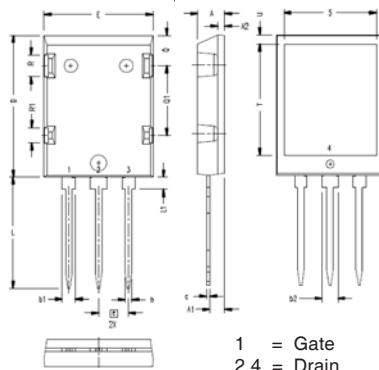
- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- AC Motor Control
- High Speed Power Switching Application

Symbol	Test Conditions (T _J = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20V, I _D = 50A, Note 1	50	80	S
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	20	nF	
C_{oss}		1700	pF	
C_{rss}		140	pF	
$t_{d(on)}$	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 50A R _G = 1Ω (External)	36	ns	
t_r		29	ns	
$t_{d(off)}$		110	ns	
t_f		26	ns	
$Q_{g(on)}$	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 50A	240	nC	
Q_{gs}		96	nC	
Q_{gd}		78	nC	
R _{thJC}			0.20 °C/W	
R _{thCS}		0.15	°C/W	

Source-Drain Diode

Symbol	Test Conditions (T _J = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I _s	V _{GS} = 0V		100	A
I _{SM}	Repetitive, Pulse Width Limited by T _{JM}		250	A
V _{SD}	I _F = I _S , V _{GS} = 0V, Note 1		1.5	V
t_{rr}	I _F = 25A, -di/dt = 100A/μs V _R = 100V, V _{GS} = 0V	0.6	200	ns
Q _{RM}			μC	
I _{RM}		6.0	A	

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ISOPLUS264 (IXFL) OUTLINE


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.087	.102	2.21	2.59
b2	.111	.126	2.82	3.20
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.799	19.56	20.29
e	.215 BSC		5.46 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

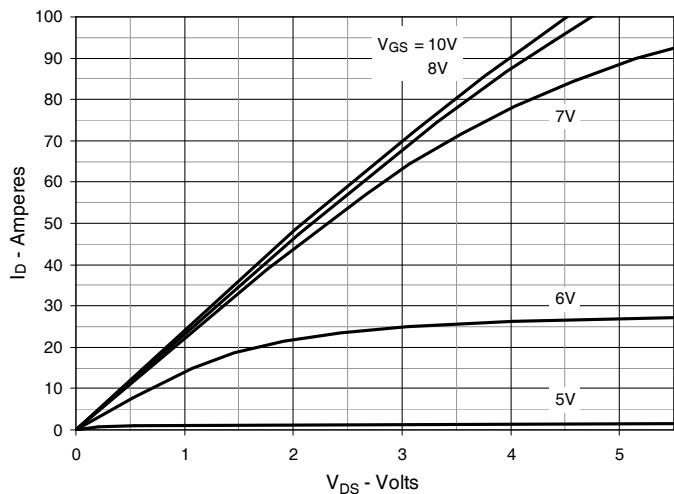
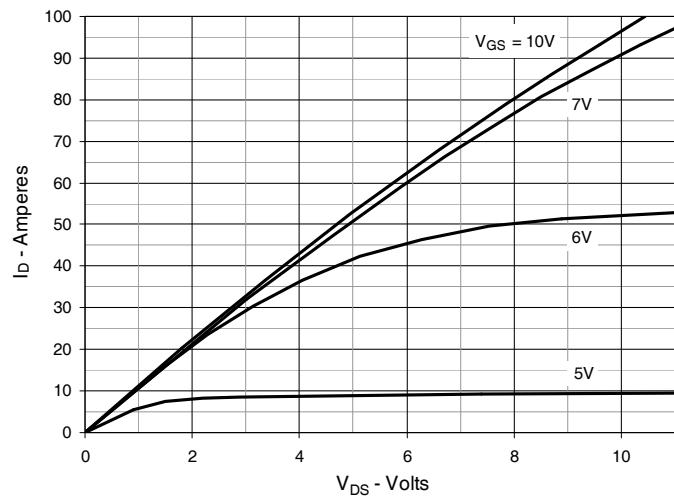
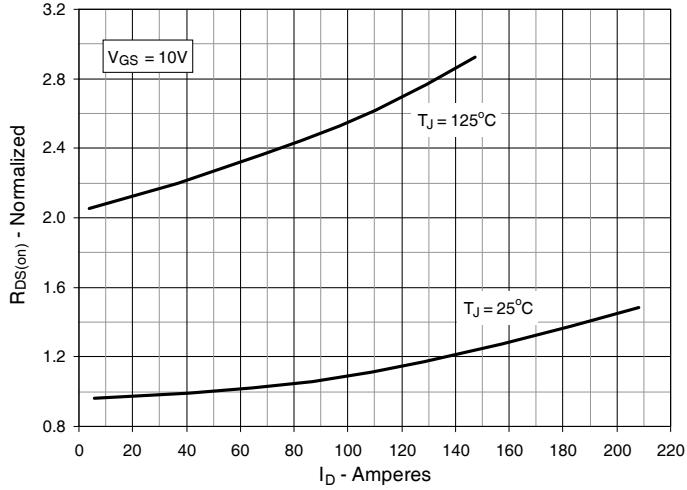
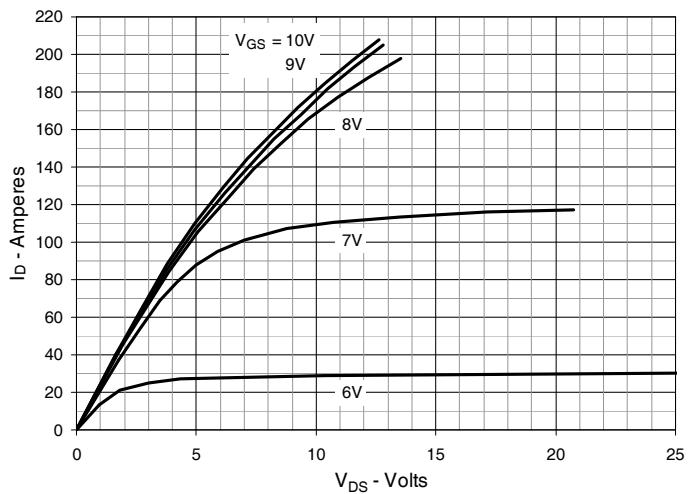
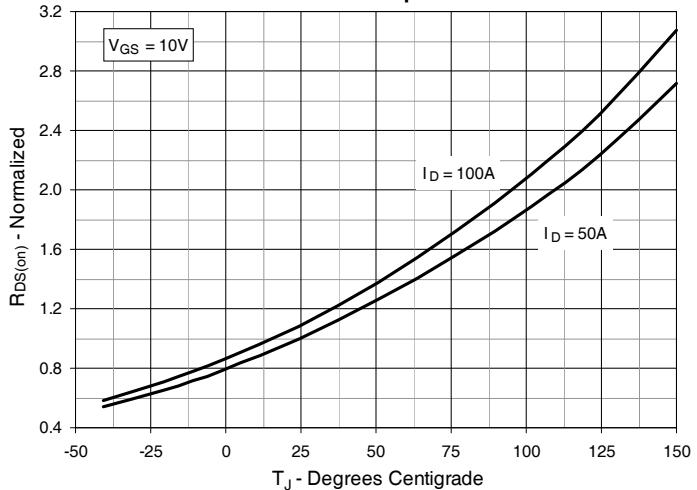
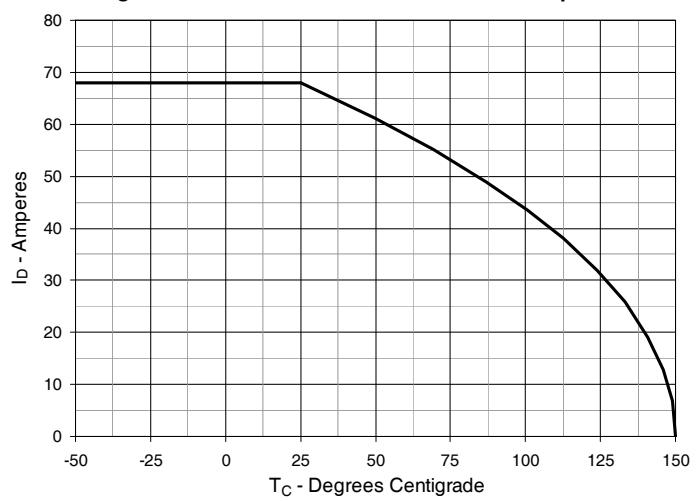
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 50\text{A}$ Value vs. Drain Current****Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$** **Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 50\text{A}$ Value vs. Junction Temperature****Fig. 6. Maximum Drain Current vs. Case Temperature**

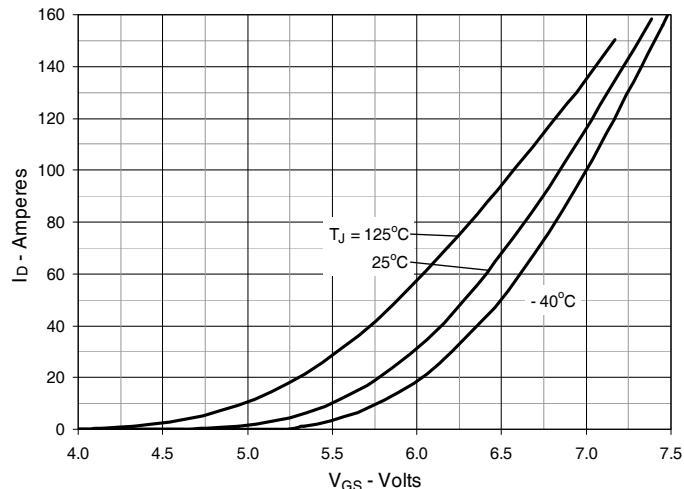
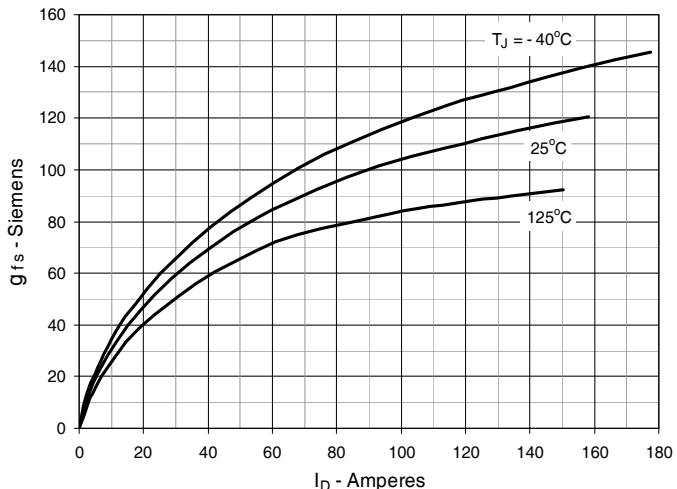
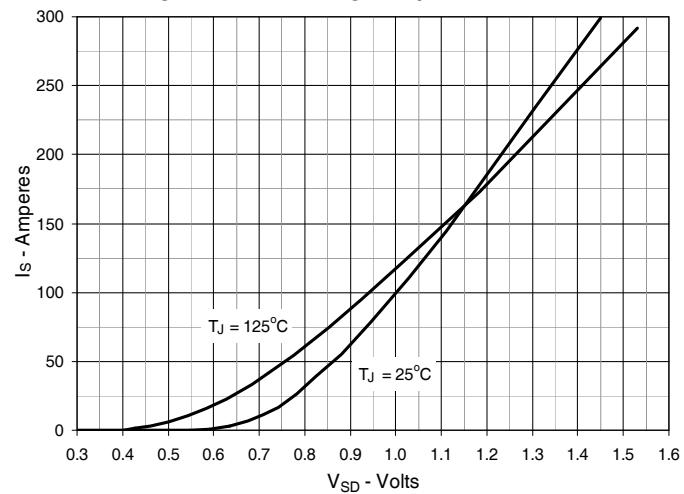
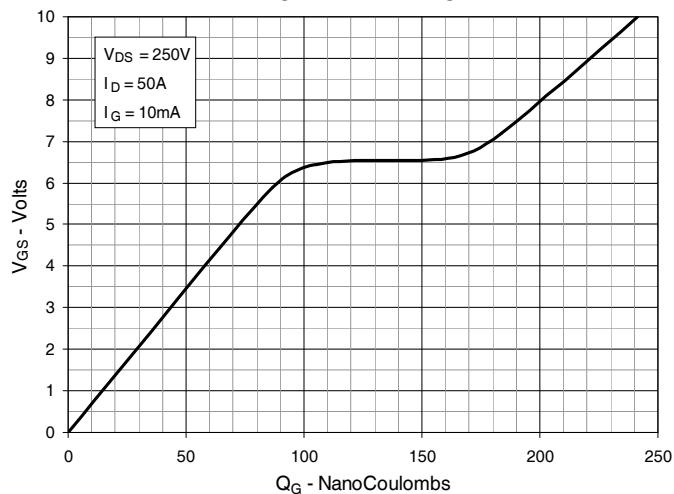
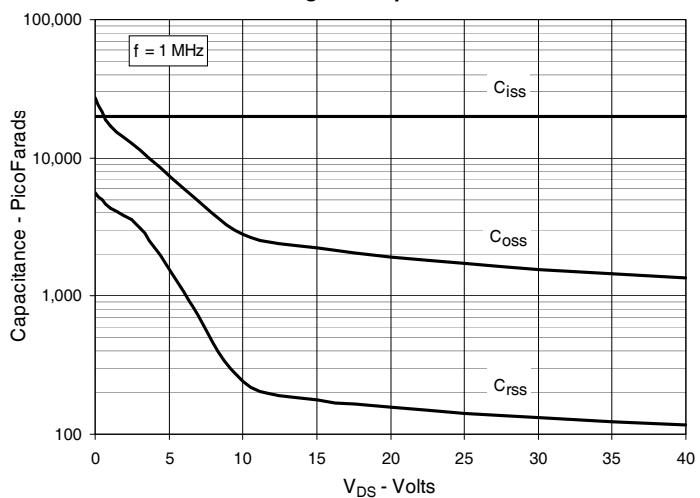
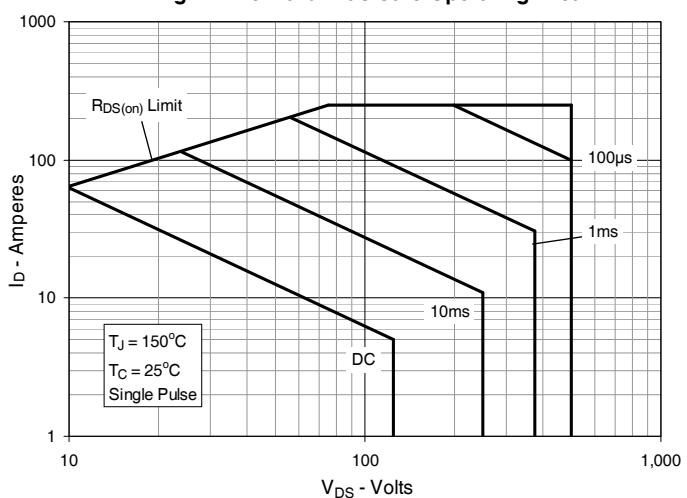
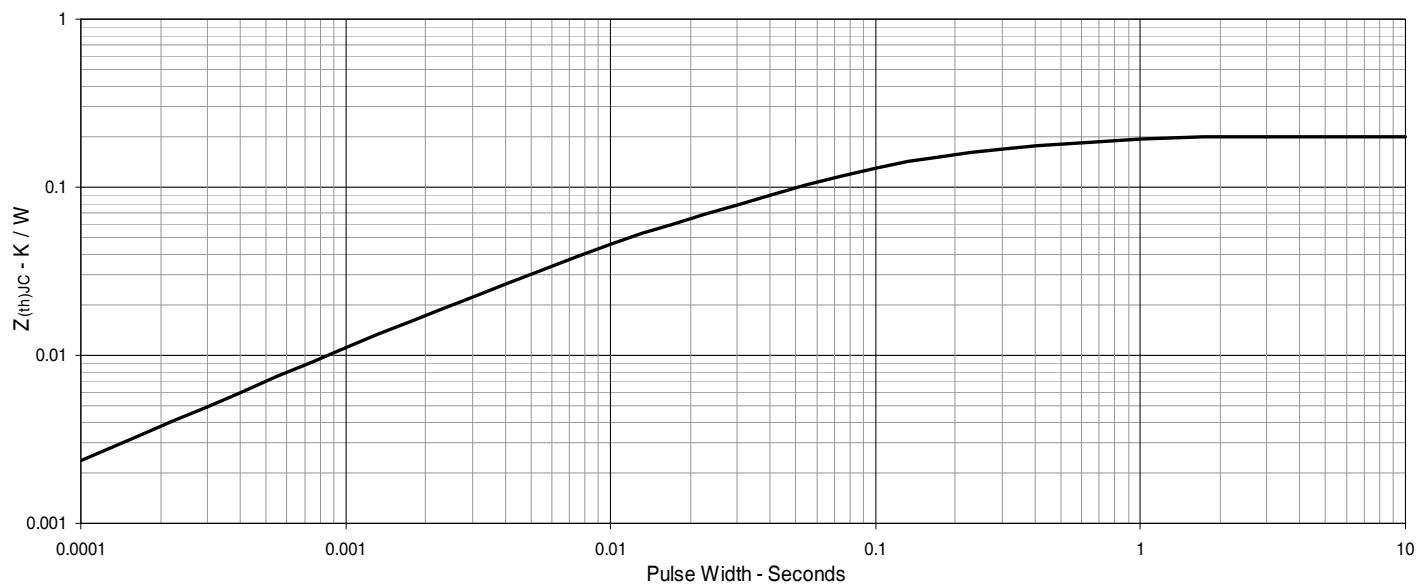
Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Forward-Bias Safe Operating Area**

Fig. 13. Maximum Transient Thermal Impedance



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